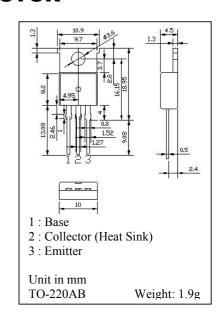


TRIPLE DIFFUSED SILICON NPN TRANSISTOR

... designed for low frequency power amplifier

MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	100	V
Collector Emitter Voltage	V _{CEO}	80	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current (DC)	Ic	4	Α
Collector Current (Peak)	I_{C}	8	Α
Collector power Dissipation	Pc	40	W
Junction Temperature	T _J	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS

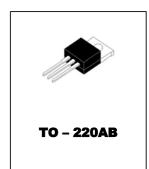
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector Cut Off Current	I_{CBO}	$V_{CB} = 80V$, $I_E = 0A$	-	-	100	μΑ
Collector – Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = 50 \text{mA}, I_B = 0 \text{A}$	80	-	-	V
DC Current Gain	h_{FE}	$V_{CE} = 4V$, $I_{C} = 1A$	60	-	200	-
		$V_{CE} = 4V$, $I_{C} = 0.1A$	35	-	-	-
Collector Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 2A$, $I_B = 0.2A$	-	-	1	V
Base Emitter Voltage	V_{BE}	$V_{CE} = 4V$, $I_{C} = 1A$	-	-	1.5	V
Transition Frequency	f_T	$V_{CE} = 5V$, $I_{C} = 0.5A$	-	10	-	MHz
Collector Out put Capacitance	C_{ob}	$V_{CB} = 20V$, $I_E = 0A$, $f=1MHz$	-	40	-	Pf

HIGH POWER
DISSIPATION

MEDIUM SPEED
POWER
SWITCHING

Classification of hFE

Rank	В	С
Range	60 to 120	100-200



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